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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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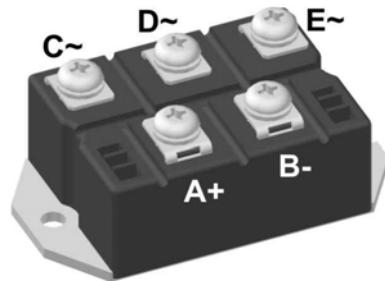
Standard Rectifier Module

3~ Rectifier
$V_{RRM} = 1600 \text{ V}$
$I_{DAV} = 125 \text{ A}$
$I_{FSM} = 1200 \text{ A}$

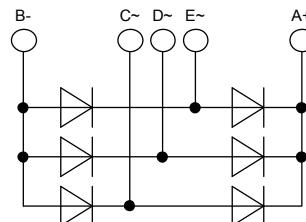
3~ Rectifier Bridge

Part number

VUO110-16NO7



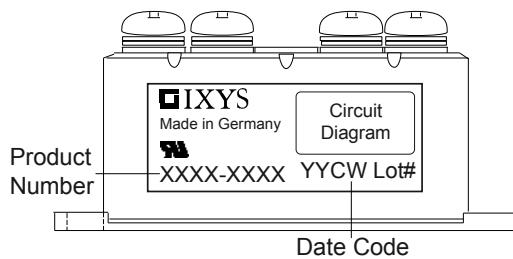
E72873



Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
I_R	reverse current	$V_R = 1600 V$ $V_R = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		100 2	μA mA
V_F	forward voltage drop	$I_F = 50 A$ $I_F = 150 A$ $I_F = 50 A$ $I_F = 150 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.13 1.46 1.04 1.47	V V
I_{DAV}	bridge output current	$T_C = 110^\circ C$ rectangular $d = \frac{1}{3}$	$T_{VJ} = 150^\circ C$		125	A
V_{FO} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.79 4.5	V $m\Omega$
R_{thJC}	thermal resistance junction to case				0.7	K/W
R_{thCH}	thermal resistance case to heatsink				0.3	K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		175	W
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 45^\circ C$ $V_R = 0 V$		1.20 1.30	kA kA
		$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 150^\circ C$ $V_R = 0 V$		1.02 1.10	kA kA
I^2t	value for fusing	$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 45^\circ C$ $V_R = 0 V$		7.20 6.98	kA^2s kA^2s
		$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 150^\circ C$ $V_R = 0 V$		5.20 5.04	kA^2s kA^2s
C_J	junction capacitance	$V_R = 400 V; f = 1 MHz$	$T_{VJ} = 25^\circ C$		37	pF

Package PWS-E			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{stg}	storage temperature		-40		125	°C
T_{vJ}	virtual junction temperature		-40		150	°C
Weight				284		g
M_D	mounting torque		4.25		5.75	Nm
M_T	terminal torque		4.25		5.75	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	12.0			mm
$d_{Spb/Apb}$		terminal to backside	26.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000 2500			V V

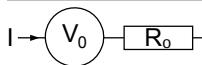


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO110-16NO7	VUO110-16NO7	Box	5	462403

Equivalent Circuits for Simulation

* on die level

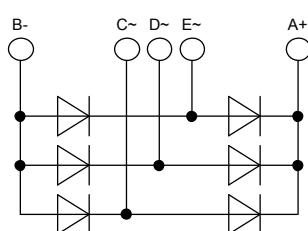
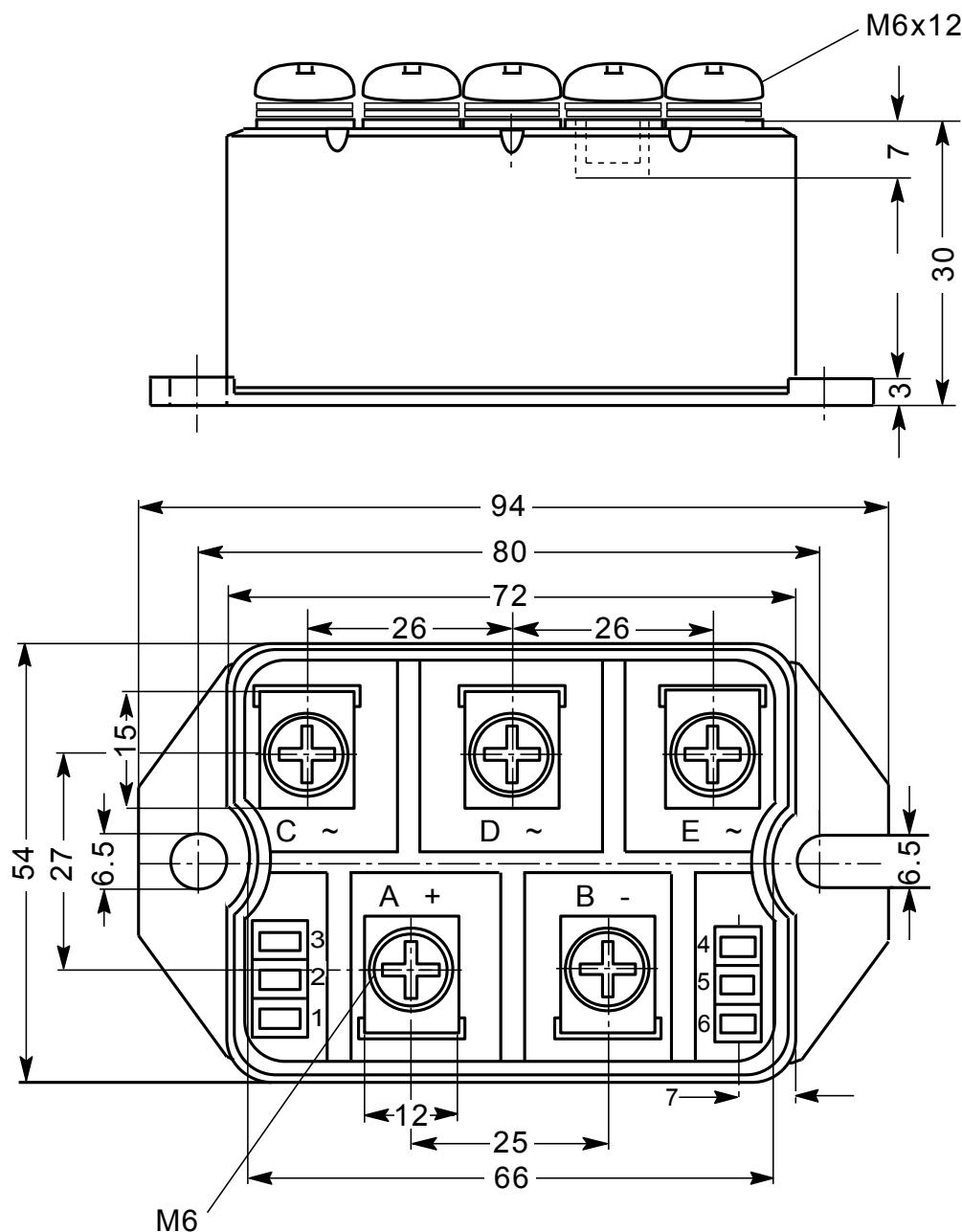
$T_{vJ} = 150$ °C



Rectifier

$V_{0\max}$ threshold voltage 0.79 V
 $R_{0\max}$ slope resistance * 3.3 mΩ

Outlines PWS-E



Rectifier

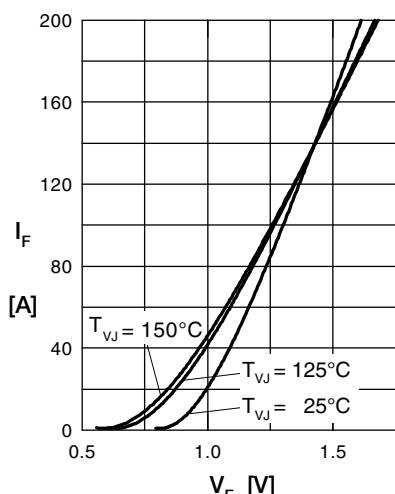


Fig. 1 Forward current vs. voltage drop per diode

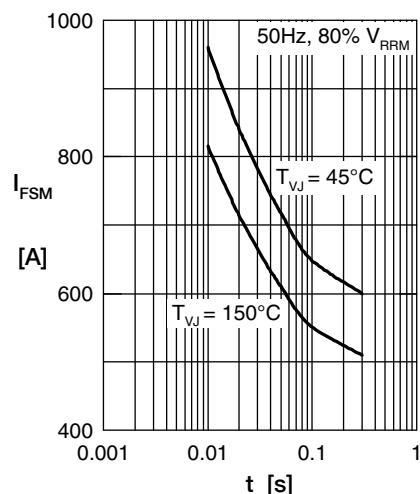


Fig. 2 Surge overload current vs. time per diode

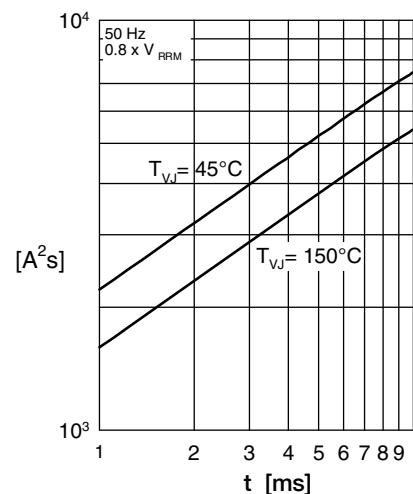
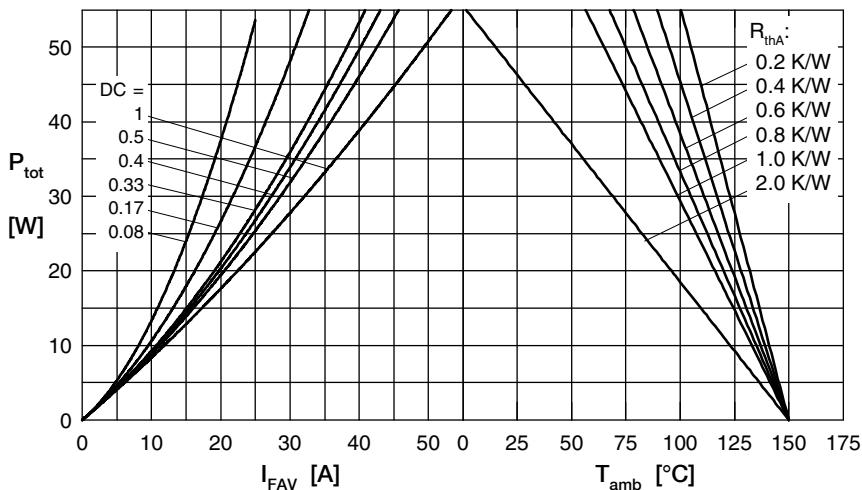
Fig. 3 I^2t vs. time per diode

Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

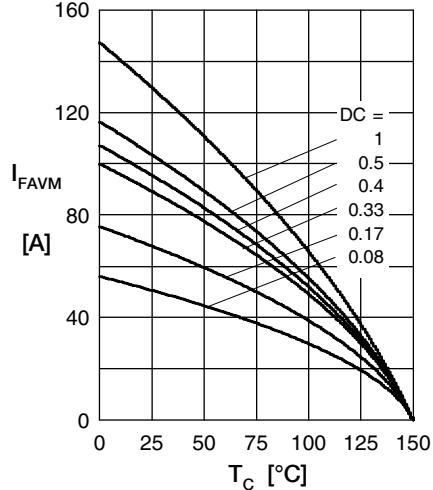


Fig. 5 Max. forward current vs. case temperature per diode

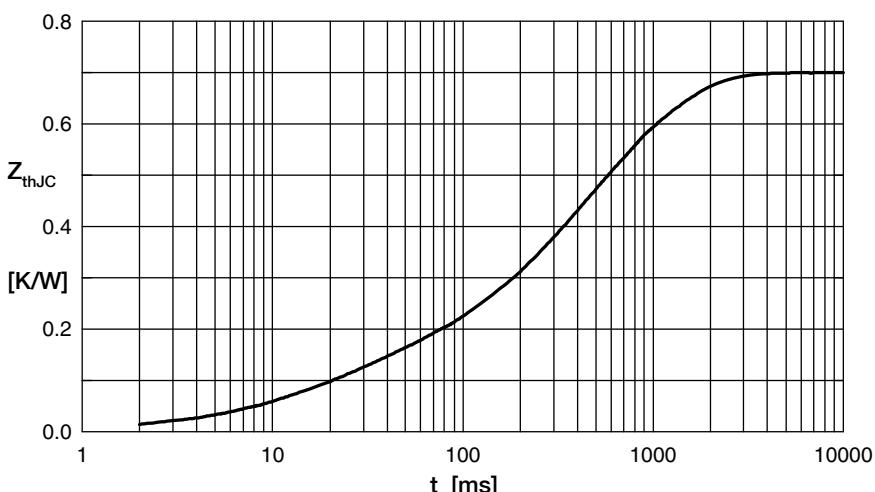


Fig. 6 Transient thermal impedance junction to case vs. time per diode

R_i	t_i
0.100	0.020
0.010	0.010
0.162	0.225
0.258	0.800
0.170	0.580